Abstract Submitted
for the MAR11 Meeting of
The American Physical Society

Device fabrication progress on epitaxial graphene on SiC YIKE HU, ZELEI GUO, RUI DONG, CLAIRE BERGER, WALT DEHEER, Georgia Tech — Epitaxial graphene on SiC has been demonstrated to be a viable route toward electronic device fabrication. While a top gate is required to locally change doping density and carrier type, specifically for field effect transistors graphene devices, back gating is relevant to globally change carrier and to address the graphene layer at the SiC-graphene interface. Here we report result on back-gating and top-gating epitaxial graphene grown on SiC by the confinement controlled sublimation method. Post-patterning treatments of graphene devices are also discussed.

Yike Hu
Georgia Tech

Date submitted: 19 Nov 2010 Electronic form version 1.4